



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

GROUP 1700

In re Appln. Of: ITO

Serial No.: 09/940,247

Filed: August 27, 2001

For: METHOD FOR FORMING A SILICIDE LAYER

Group: 2360

Examiner: LAN VINH

DOCKET: NEC 2360

Assistant Commissioner of Patents & Trademarks
Washington, D.C. 20231

AMENDMENT A

Dear Sir:

This Amendment is being filed in response to the Official Action mailed
January 29, 2003.

Please amend the Application as follows:

IN THE SPECIFICATION:

Please replace the paragraph beginning at page 1, line 12, with the following rewritten
paragraph:

--In implementing a high-speed shallow-junction device or mixed DRAM/logic device,
the achievement of low-resistivity source and drain electrodes using a salicide (self-aligned
silicide) process is essential, and from the standpoint of the fact that the width of lines formed on
a substrate is extremely narrow and immunity to heat, cobalt salicide technology is used. In a
salicide reaction process, if an impurity for suppressing a silicide reaction exists, local regions
occur in which a cobalt silicide region of uniformly low resistivity is not formed.--

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ATTORNEY

FOR THE APPLICANT

BY: HAYES SOLOWAY P.C.

DATE: 09/10/03